

ABSTRACT

In a production process for a semiconductor device employing an SiC semiconductor substrate (1), the SiC semiconductor substrate (1) is mounted on a susceptor (23), and a C heating member (3) of carbon is placed on a surface of the SiC semiconductor substrate (1). An annealing process is performed to form an impurity region in the surface of the SiC semiconductor substrate (1) by causing the susceptor (23) and the C heating member (3) to generate heat at high temperatures.